SHI LING® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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Specifcation of products

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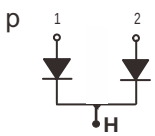
UltraFast Soft RecoveryDiode Module

Description

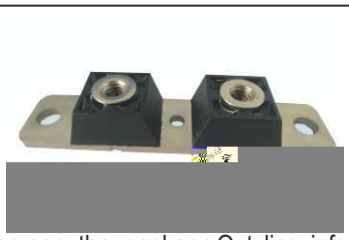
Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motors drives and other applications where switching losses are critical for efficiency

Equivalent Circuitand Package

Equivalent Circuit



Package



Please see the package Out line information

T_j

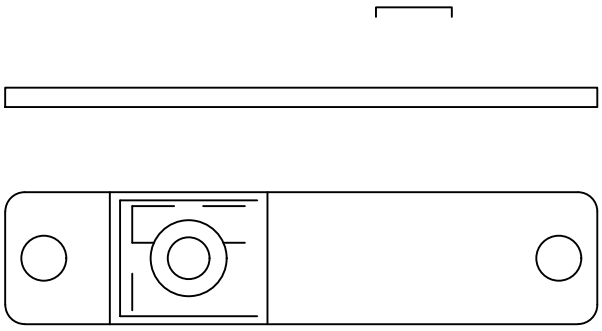
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Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.15	℃/W

Electrical Characteristics @ T_j=25℃ (unless otherwise specified)

Symbol	Parameter	Conditions		Values			Unit
				Min.	Typ.	Max.	
V_R	Cathode Anode Breakdown Voltage	I_R = 100uA		600	-	-	V
V_{FM}	Maximum Forward Voltage	I_{FM}= 200A, T_c= 25℃		-	1.0	1.1	V
		I_{FM} = 200A, T_c=100℃		-	0.9	1.0	V
I_{RRM}	Repetitive Peak Reverse Current	T_C= 100℃, V_{RRM} applied		-	-	8.5	mA
T_{rr}	Reverse Recovery Time	I_{FM}= 200A, V_R= 300V di/dt=-100A/us	T_C= 25℃	-	95	100	ns
			T_C= 100℃	-	180	-	ns



Rating and Characteristic

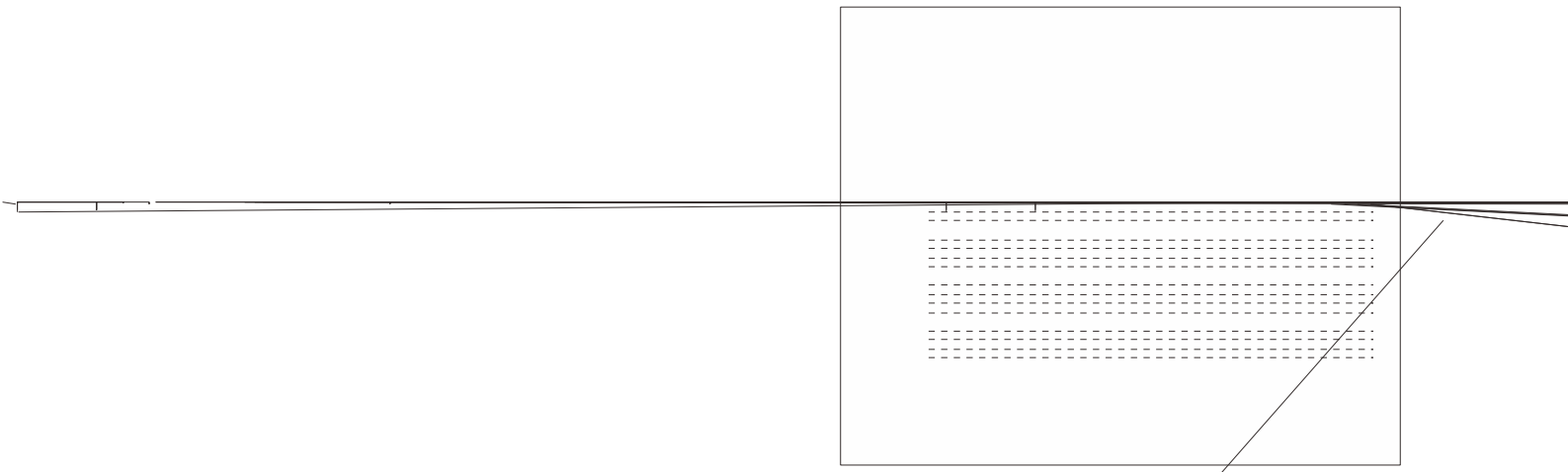


Fig. 2 : Typical Reverse Recovery Time vs. -di/dt